

**Listing of the Claims**

Claims 1-10 (Canceled).

11. (Currently Amended): Silicon-on-insulator comprising integrated circuitry, comprising:

a substrate comprising a semiconductive ~~silicon-comprising~~ silicon-comprising layer of silicon-on-insulator circuitry, the ~~silicon-comprising~~ semiconductive silicon-comprising layer comprising a pair of source/drain regions formed therein and a channel region formed therein which is received intermediate the source/drain regions;

a transistor gate received operably proximate the channel region; and

an insulator layer of the silicon-on-insulator circuitry received on the ~~silicon-comprising~~ semiconductive silicon-comprising layer, the insulator layer comprising a first ~~silicon-dioxide-comprising~~ silicon dioxide-comprising region in contact with the ~~silicon-comprising~~ semiconductive silicon-comprising layer and running along at least a portion of the channel region between the source/drain regions, a ~~silicon-nitride-comprising~~ silicon nitride-comprising region in contact with the first ~~silicon-dioxide-comprising~~ silicon dioxide-comprising region and running along only a portion of the channel region, and a second ~~silicon-dioxide-comprising~~ silicon dioxide-comprising region in contact with the ~~silicon-nitride-comprising~~ silicon nitride-comprising region, the ~~silicon-nitride-comprising~~ silicon nitride-comprising region being received intermediate the first and second ~~silicon-dioxide-comprising~~ silicon dioxide-comprising regions.

Claims 12 and 13 (Canceled).

14. (Currently Amended): The circuitry of claim 11 wherein the ~~silicon nitride-comprising~~ silicon nitride-comprising region has a thickness of from about 10 Angstroms to about 50 Angstroms.

15. (Currently Amended): The circuitry of claim 11 wherein the first ~~silicon dioxide-comprising~~ silicon dioxide-comprising region has a thickness of from about 10 Angstroms to about 30 Angstroms.

16. (Original): The circuitry of claim 11 wherein the source/drain regions extend to the insulator layer.

Claim 17-61 (Canceled).

62. (Currently Amended): Silicon-on-insulator comprising integrated circuitry, comprising:

a substrate comprising a semiconductive ~~silicon-comprising~~ silicon-comprising layer of silicon-on-insulator circuitry, the ~~silicon-comprising~~ semiconductive silicon-comprising layer comprising a pair of source/drain regions formed therein and a channel region formed therein which is received intermediate the source/drain regions;

a transistor gate received operably proximate the channel region; and

an insulator layer of the silicon-on-insulator circuitry received on the ~~silicon-comprising~~ semiconductive silicon-comprising layer, the insulator layer comprising a first ~~silicon-dioxide-comprising~~ silicon dioxide-comprising region in contact with the ~~silicon-comprising~~ semiconductive silicon-comprising layer and running along at least a portion of the channel region between the source/drain regions, a ~~silicon-oxynitride-comprising~~ silicon oxynitride-comprising region in contact with the first ~~silicon-dioxide-comprising~~ silicon dioxide-comprising region and running along only a portion of the channel region, and a second ~~silicon-dioxide-comprising~~ silicon dioxide-comprising region in contact with the ~~silicon-oxynitride-comprising~~ silicon oxynitride-comprising region, the ~~silicon-oxynitride-comprising~~ silicon oxynitride-comprising region being received intermediate the first and second ~~silicon-dioxide-comprising~~ silicon dioxide-comprising regions.

63. (Currently Amended): The circuitry of claim 62 wherein the ~~silicon oxynitride-comprising~~ silicon oxynitride-comprising region has a thickness of from about 10 Angstroms to about 50 Angstroms.

64. (Currently Amended): The circuitry of claim 62 wherein the first ~~silicon dioxide-comprising~~ silicon dioxide-comprising region has a thickness of from about 10 Angstroms to about 30 Angstroms.

65. (Previously Presented): The circuitry of claim 62 wherein the source/drain regions extend to the insulator layer.

66. (Currently Amended): The circuitry of claim 62 wherein the ~~silicon comprising~~ semiconductive silicon-comprising layer has a thickness from about 1000 Angstroms to about 2000 Angstroms.

67. (Currently Amended): The circuitry of claim 11 wherein the ~~silicon comprising~~ semiconductive silicon-comprising layer has a thickness from about 1000 Angstroms to about 2000 Angstroms.